

# Q1PACK Module

## NXH75M65L4Q1SG, NXH75M65L4Q1PTG

This high-density, integrated power module combines high-performance IGBTs with rugged anti-parallel diodes.

### Features

- Extremely Efficient Trench with Fieldstop Technology
- Low Switching Loss Reduces System Power Dissipation
- Module Design Offers High Power Density
- Low Inductive Layout
- Q1PACK Packages with Solder and Pressfit Pins

### Typical Applications

- Solar Inverters
- Uninterruptable Power Supplies

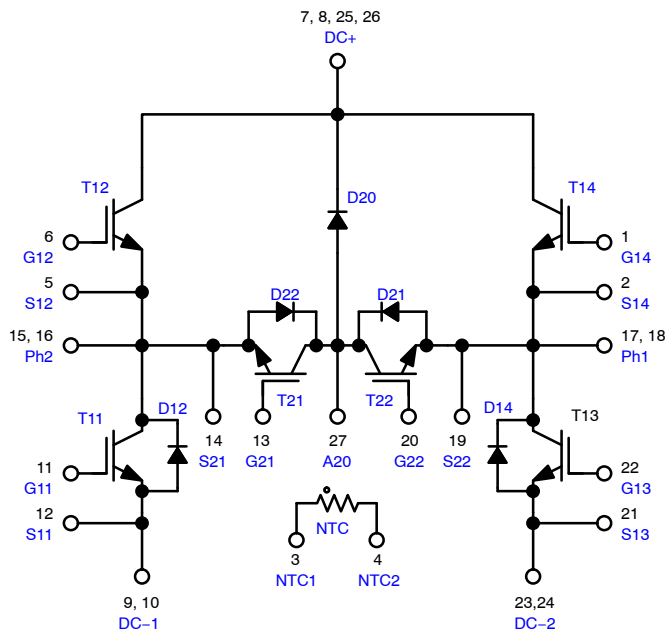


Figure 1. Schematic

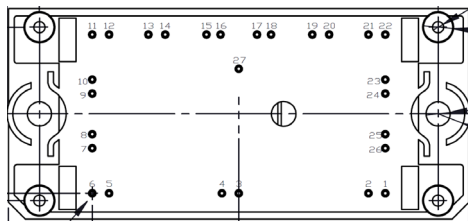
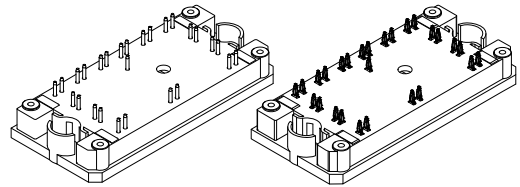


Figure 2. Pin Assignments

### 75 A, 650 V Module



PIM27, 71x37.4  
(SOLDER PIN)  
CASE 180CA

PIM27, 71x37.4  
(PRESSFIT PIN)  
CASE 180CP

### MARKING DIAGRAM



XXXXXX = Specific Device Code  
G = Pb-Free Package  
AT = Assembly & Test Site Code  
YYWW = Year and Work Week Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 9 of this data sheet.

# NXH75M65L4Q1SG, NXH75M65L4Q1PTG

## ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
<b>IGBT (T11, T12, T13, T14, T21, T22)</b>			
Collector-emitter voltage	$V_{CES}$	650	V
Collector current @ $T_h = 80^\circ\text{C}$ (per IGBT)	$I_C$	59	A
Pulsed collector current, $T_{\text{pulse}}$ limited by $T_{j\text{max}}$	$I_{CM}$	176	A
Power Dissipation Per IGBT $T_j = T_{j\text{max}}, T_h = 80^\circ\text{C}$	$P_{\text{tot}}$	83	W
Gate-emitter voltage	$V_{GE}$	$\pm 20$	V
Maximum Junction Temperature	$T_J$	175	$^\circ\text{C}$

## DIODE (D12, D14, D20, D21, D22)

Peak Repetitive Reverse Voltage	$V_{RRM}$	650	V
Forward Current, DC @ $T_h = 80^\circ\text{C}$ (per Diode)	$I_F$	50	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	$I_{FSM}$	225	A
Power Dissipation Per Diode $T_j = T_{j\text{max}}, T_h = 80^\circ\text{C}$	$P_{\text{tot}}$	86	W
Maximum Junction Temperature	$T_J$	175	$^\circ\text{C}$

## THERMAL PROPERTIES

Operating Temperature under switching condition	$T_{VJ\text{OP}}$	-40 to ( $T_{j\text{max}} - 25$ )	$^\circ\text{C}$
Storage Temperature range	$T_{\text{stg}}$	-40 to 125	$^\circ\text{C}$

## INSULATION PROPERTIES

Isolation test voltage, $t = 2$ min, 60 Hz	$V_{\text{is}}$	4000	Vac
Creepage distance		12.7	mm

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Test Condition	Symbol	Min	Typ	Max	Unit
<b>IGBT (T11, T12, T13, T14, T21, T22)</b>						
Collector-emitter cutoff current	$V_{GE} = 0\text{ V}, V_{CE} = 650\text{ V}$	$I_{CES}$	-	-	300	$\mu\text{A}$
Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 75\text{ A}, T_j = 25^\circ\text{C}$ $V_{GE} = 15\text{ V}, I_C = 75\text{ A}, T_j = 150^\circ\text{C}$	$V_{CE(\text{sat})}$	-	1.56 1.76	2.22 -	V
Gate-emitter threshold voltage	$V_{GE} = V_{CE}, I_C = 75\text{ mA}$	$V_{GE(\text{TH})}$	3.1	4.45	5.2	V
Gate leakage current	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	$I_{GES}$	-	-	400	nA
Turn-on delay time	$T_j = 25^\circ\text{C}$ $V_{CE} = 350\text{ V}, I_C = 80\text{ A}$ $V_{GE} = 15\text{ V}, -9\text{ V}, R_G = 10\ \Omega$	$t_{d(\text{on})}$	-	38	-	ns
Rise time		$t_r$	-	34	-	
Turn-off delay time		$t_{d(\text{off})}$	-	129	-	
Fall time		$t_f$	-	17	-	
Turn on switching loss		$E_{\text{on}}$	-	0.606	-	mJ
Turn off switching loss		$E_{\text{off}}$	-	0.903	-	
Turn-on delay time	$T_j = 125^\circ\text{C}$ $V_{CE} = 350\text{ V}, I_C = 80\text{ A}$ $V_{GE} = 15\text{ V}, -9\text{ V}, R_G = 10\ \Omega$	$t_{d(\text{on})}$	-	37	-	ns
Rise time		$t_r$	-	34	-	
Turn-off delay time		$t_{d(\text{off})}$	-	139	-	
Fall time		$t_f$	-	23	-	
Turn on switching loss		$E_{\text{on}}$	-	1.024	-	mJ
Turn off switching loss		$E_{\text{off}}$	-	1.141	-	

# NXH75M65L4Q1SG, NXH75M65L4Q1PTG

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified) (continued)

Parameter	Test Condition	Symbol	Min	Typ	Max	Unit
<b>IGBT (T11, T12, T13, T14, T21, T22)</b>						
Input capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	$C_{ies}$	–	5665	–	pF
Output capacitance		$C_{oes}$	–	205	–	
Reverse transfer capacitance		$C_{res}$	–	100	–	
Gate charge total	$V_{CE} = 480\text{ V}, I_C = 50\text{ A}, V_{GE} = \pm 15\text{ V}$	$Q_g$	–	550	–	nC
Thermal Resistance – chip-to-heatsink	Thermal grease, Thickness = 2.1 Mil $\pm 2\%$ $\lambda = 2.9\text{ W/mK}$	$R_{thJH}$	–	1.15	–	$^\circ\text{C/W}$
Thermal Resistance – chip-to-case		$R_{thJC}$	–	0.75	–	$^\circ\text{C/W}$

## IGBT INVERSE DIODE (D12, D14, D21, D22)

Forward voltage	$I_F = 50\text{ A}, T_J = 25^\circ\text{C}$ $I_F = 50\text{ A}, T_J = 175^\circ\text{C}$	$V_F$	–	2.25 1.7	2.7 –	V
Reverse Recovery Time	$T_J = 25^\circ\text{C}$ $V_{CE} = 350\text{ V}, I_C = 80\text{ A}$ $V_{GE} = 15\text{ V}, -9\text{ V}, R_G = 10\ \Omega$	$t_{rr}$	–	63	–	ns
Reverse Recovery Current		$Q_{rr}$	–	552	–	nC
Peak Reverse Recovery Current		$I_{rrm}$	–	25	–	A
Peak Rate of Fall of Recovery Current		$Di/dt_{max}$	–	1.80	–	A/ $\mu\text{s}$
Reverse Recovery Energy		$E_{rr}$	–	136	–	$\mu\text{J}$
Reverse Recovery Time	$T_J = 125^\circ\text{C}$ $V_{CE} = 350\text{ V}, I_C = 50\text{ A}$ $V_{GE} = 15\text{ V}, -9\text{ V}, R_G = 10\ \Omega$	$t_{rr}$	–	135	–	ns
Reverse Recovery Current		$Q_{rr}$	–	1538	–	nC
Peak Reverse Recovery Current		$I_{rrm}$	–	43	–	A
Peak Rate of Fall of Recovery Current		$Di/dt_{max}$	–	1.60	–	A/ $\mu\text{s}$
Reverse Recovery Energy		$E_{rr}$	–	346	–	$\mu\text{J}$
Thermal Resistance – chip-to-heatsink	Thermal grease, Thickness = 2.1 Mil $\pm 2\%$ $\lambda = 2.9\text{ W/mK}$	$R_{thJH}$	–	1.10	–	$^\circ\text{C/W}$
Thermal Resistance – chip-to-case		$R_{thJC}$	–	0.79	–	$^\circ\text{C/W}$

## DIODE (D20)

Forward voltage	$I_F = 50\text{ A}, T_J = 25^\circ\text{C}$ $I_F = 50\text{ A}, T_J = 175^\circ\text{C}$	$V_F$	–	2.25 1.7	2.7 –	V
Reverse leakage current	$V_{CE} = 650\text{ V}, V_{GE} = 0\text{ V}$	$I_r$	–	–	300	$\mu\text{A}$
Thermal Resistance – chip-to-heatsink	Thermal grease, Thickness = 2.1 Mil $\pm 2\%$ $\lambda = 2.9\text{ W/mK}$	$R_{thJH}$	–	1.10	–	$^\circ\text{C/W}$
Thermal Resistance – chip-to-case		$R_{thJC}$	–	0.79	–	$^\circ\text{C/W}$

## THERMISTOR CHARACTERISTICS

Nominal resistance	$T = 25^\circ\text{C}$	$R_{25}$	–	22	–	k $\Omega$
Nominal resistance	$T = 100^\circ\text{C}$	$R_{100}$	–	1486	–	$\Omega$
Deviation of $R_{25}$		$R/R$	–5	–	5	%
Power dissipation		$P_D$	–	200	–	mW
Power dissipation constant			–	2	–	mW/ $^\circ\text{C}$
B-value	B (25/50), tol $\pm 3\%$		–	–	3950	$^\circ\text{C}$
B-value	B (25/100), tol $\pm 3\%$		–	–	3998	$^\circ\text{C}$
NTC reference			–	–	B	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# NXH75M65L4Q1SG, NXH75M65L4Q1PTG

## TYPICAL CHARACTERISTICS – IGBT (T11, T12, T13, T14, T21, T22)

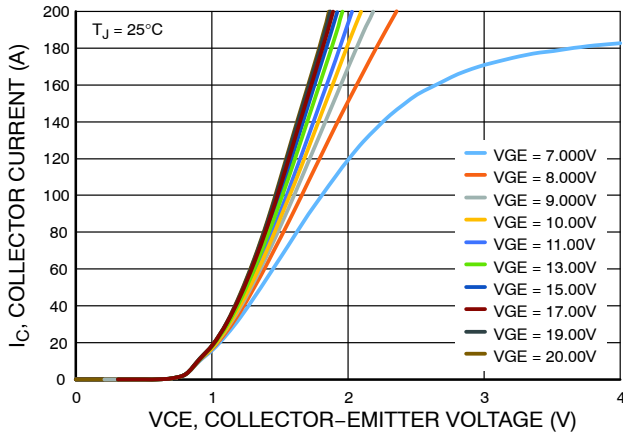


Figure 3. Typical Output Characteristics

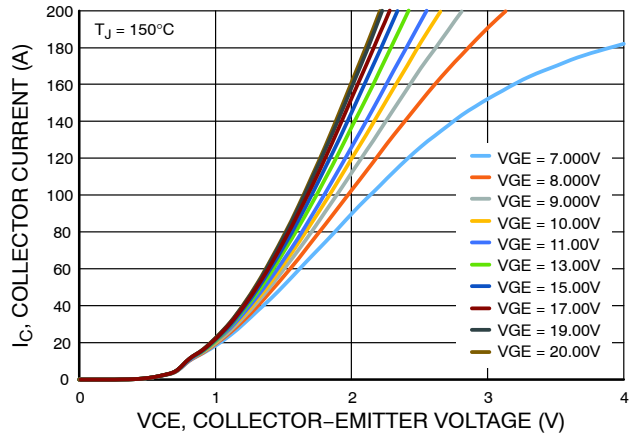


Figure 4. Typical Output Characteristics

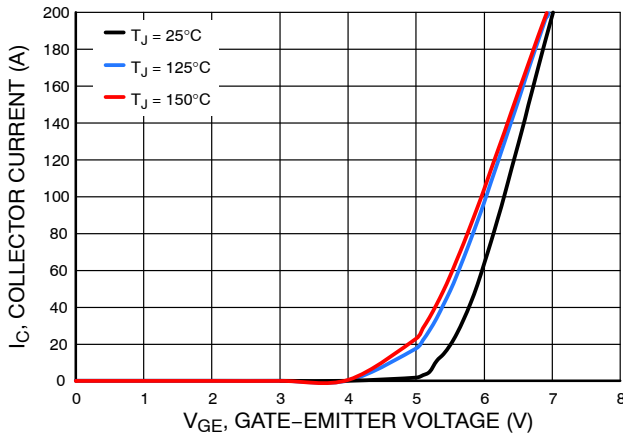


Figure 5. Typical Transfer Characteristics

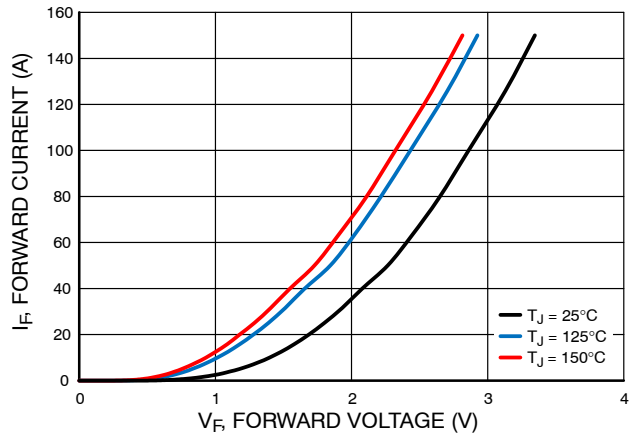


Figure 6. Diode Forward Characteristics

## TYPICAL CHARACTERISTICS – (T11, T12, T13, T14) IGBT COMMUTATES D21, D22 DIODE

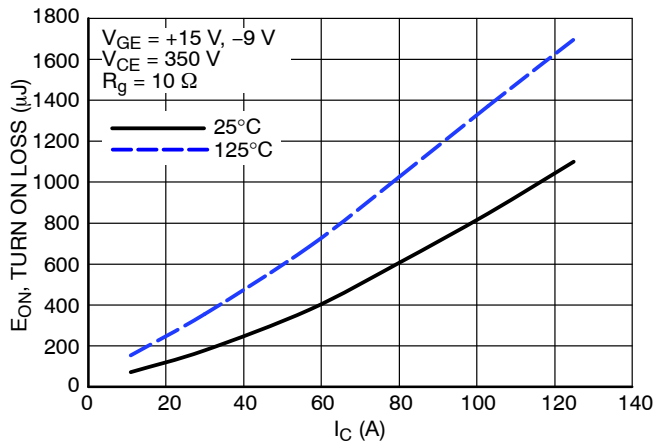


Figure 7. Typical Turn ON Loss vs. IC

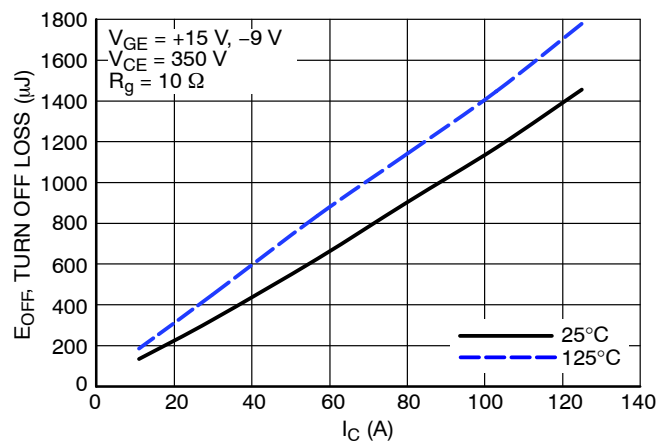
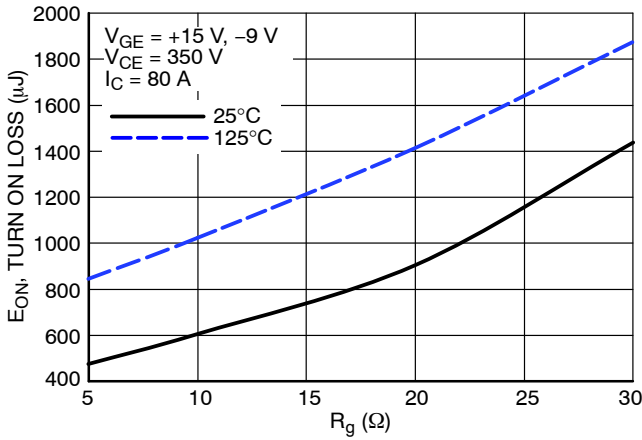


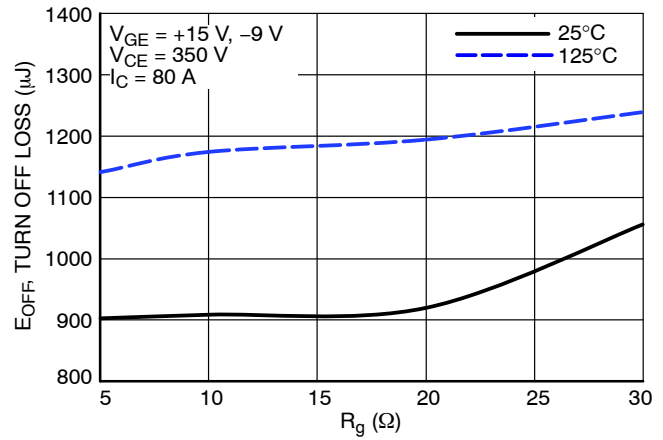
Figure 8. Typical Turn OFF Loss vs. IC

# NXH75M65L4Q1SG, NXH75M65L4Q1PTG

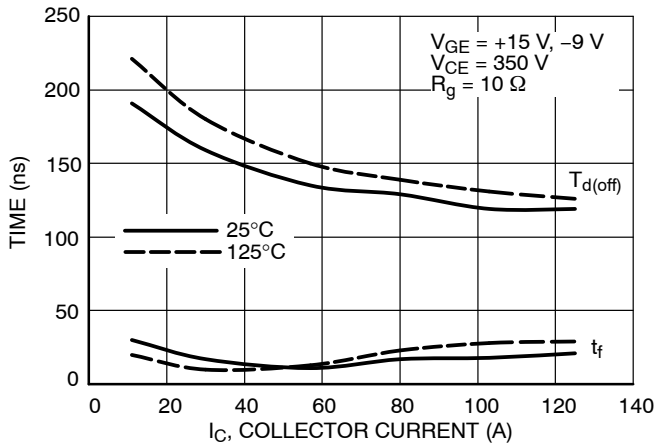
## TYPICAL CHARACTERISTICS – (T11, T12, T13, T14) IGBT COMMUTATES D21, D22 DIODE (CONTINUED)



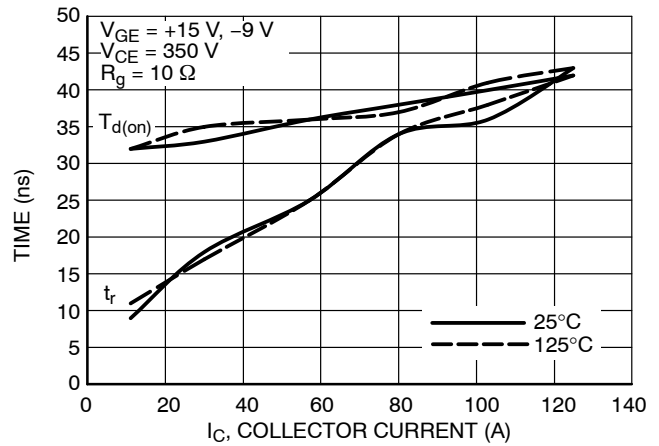
**Figure 9. Typical Turn ON Loss vs. Rg**



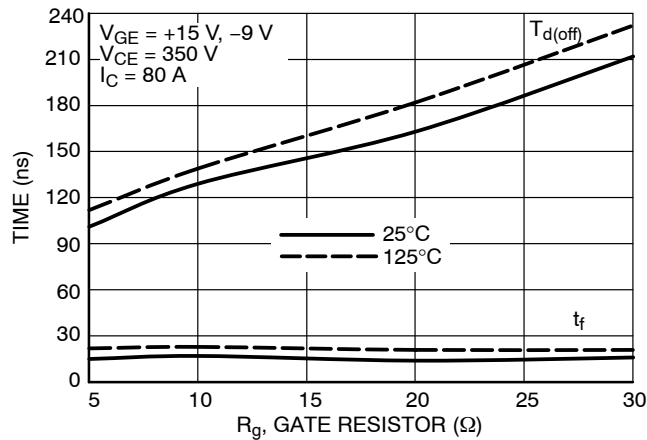
**Figure 10. Typical Turn OFF Loss vs. Rg**



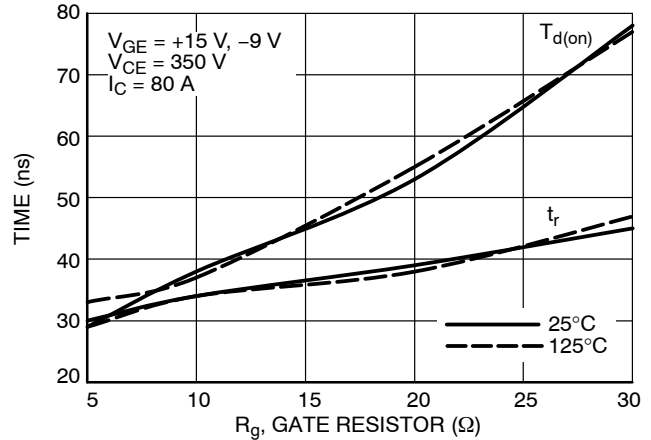
**Figure 11. Typical Turn-Off Switching Time vs. IC**



**Figure 12. Typical Turn-On Switching Time vs. IC**



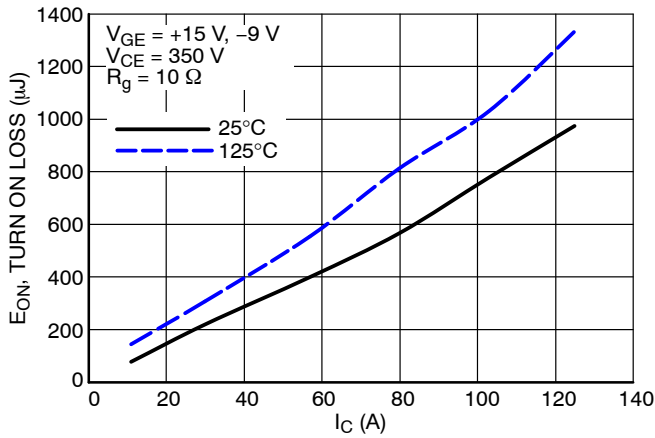
**Figure 13. Typical Turn-Off Switching Time vs. Rg**



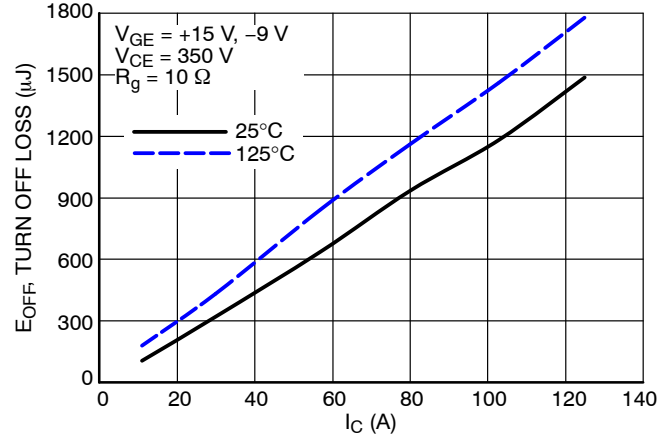
**Figure 14. Typical Turn-On Switching Time vs. Rg**

# NXH75M65L4Q1SG, NXH75M65L4Q1PTG

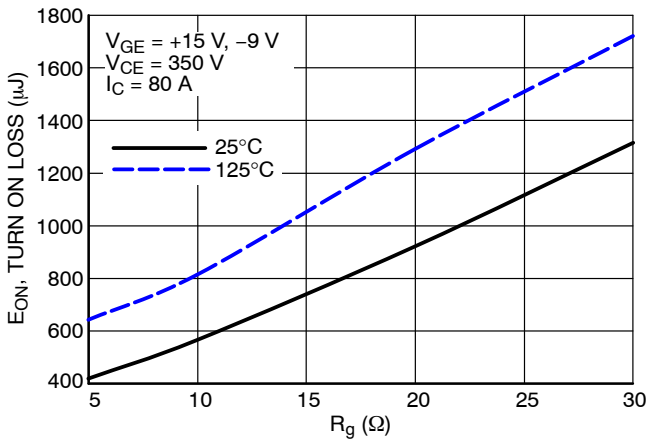
## TYPICAL CHARACTERISTICS - (T21, T22) IGBT COMMUTATES D20 DIODE



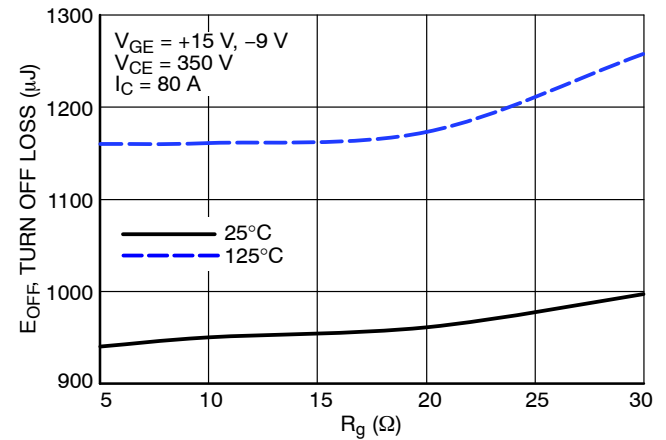
**Figure 15. Typical Turn ON Loss vs. IC**



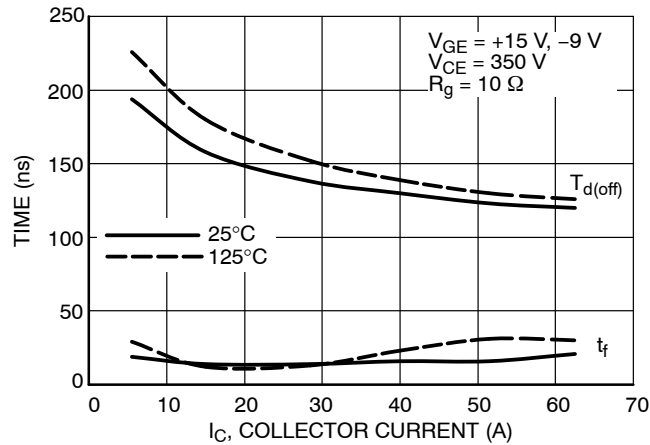
**Figure 16. Typical Turn OFF Loss vs. IC**



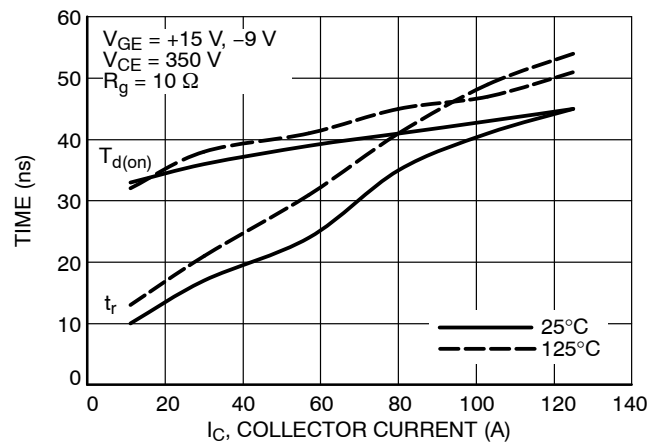
**Figure 17. Typical Turn ON Loss vs. R<sub>G</sub>**



**Figure 18. Typical Turn OFF Loss vs. R<sub>G</sub>**



**Figure 19. Typical Turn-Off Switching Time vs. IC**



**Figure 20. Typical Turn-On Switching Time vs. IC**

# NXH75M65L4Q1SG, NXH75M65L4Q1PTG

## TYPICAL CHARACTERISTICS – (T21, T22) IGBT COMMUTATES D20 DIODE (CONTINUED)

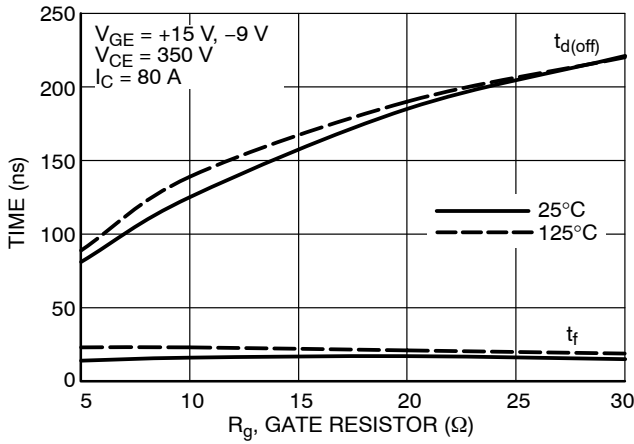


Figure 21. Typical Turn-Off Switching Time vs. Rg

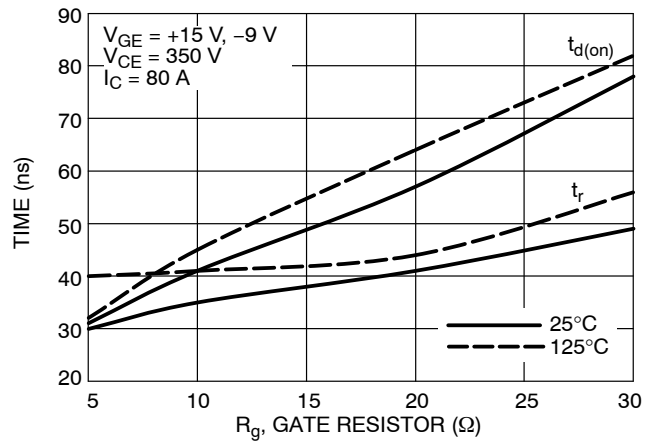


Figure 22. Typical Turn-On Switching Time vs. Rg

## TYPICAL CHARACTERISTICS – DIODE

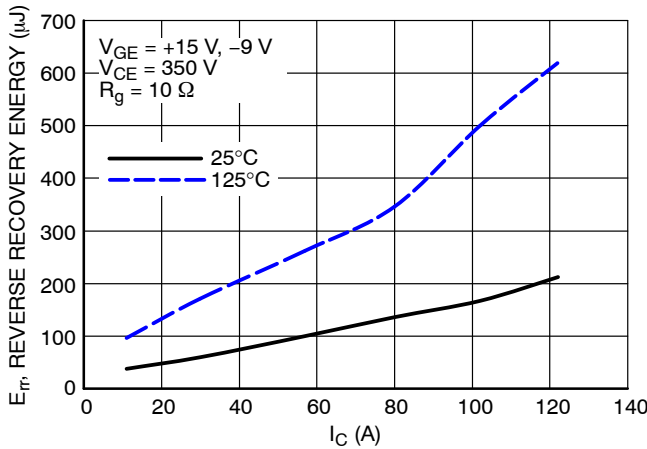


Figure 23. Typical Reverse Recovery Energy Loss vs. IC

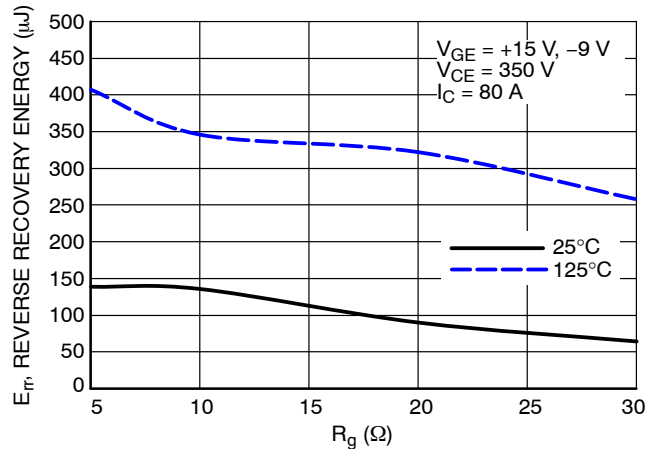


Figure 24. Typical Reverse Recovery Energy Loss vs. Rg

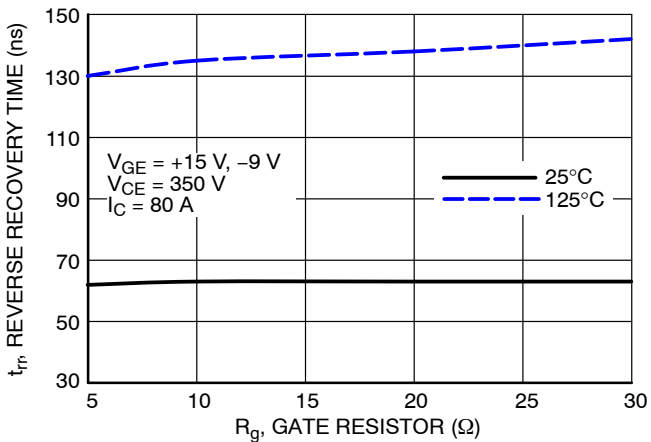


Figure 25. Typical Reverse Recovery Time vs. Rg

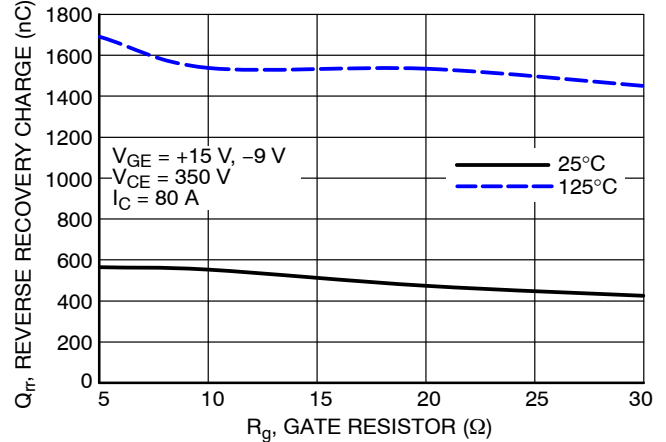


Figure 26. Typical Reverse Recovery Charge vs. Rg

# NXH75M65L4Q1SG, NXH75M65L4Q1PTG

## TYPICAL CHARACTERISTICS – DIODE (CONTINUED)

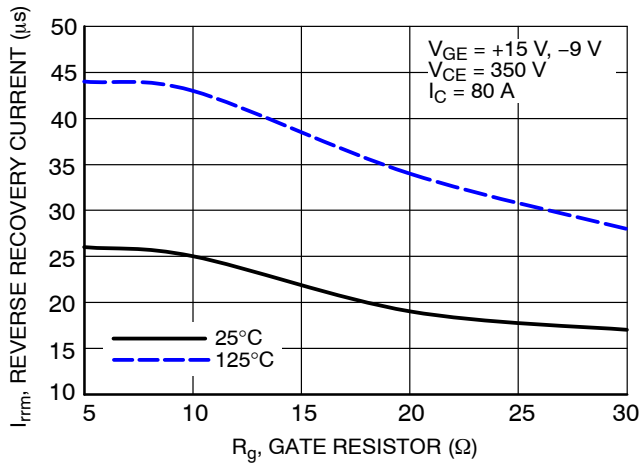


Figure 27. Typical Reverse Recovery Peak Current vs. Rg

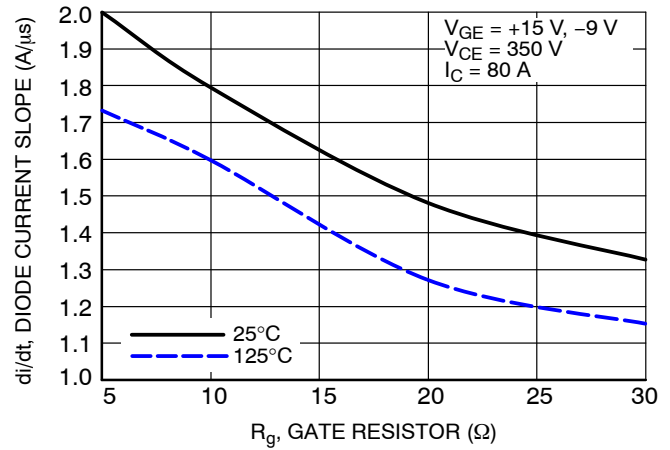


Figure 28. Typical di/dt vs. Rg

## TYPICAL CHARACTERISTICS

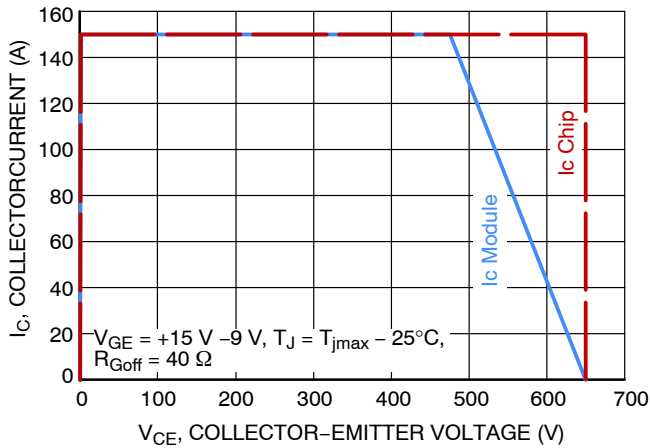


Figure 29. RBSOA Reverse Safe Operating Area

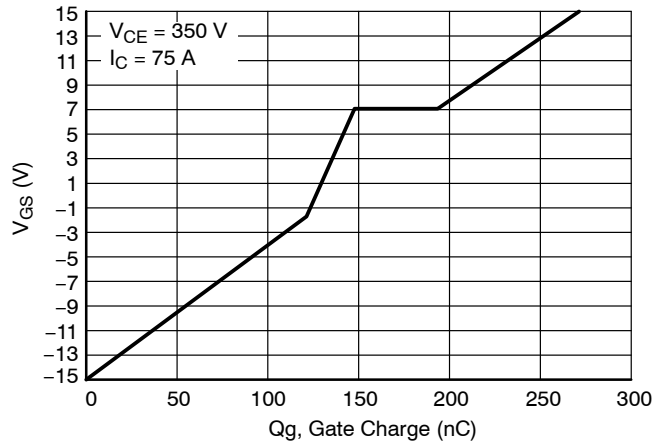


Figure 30. IGBT Gate Charge

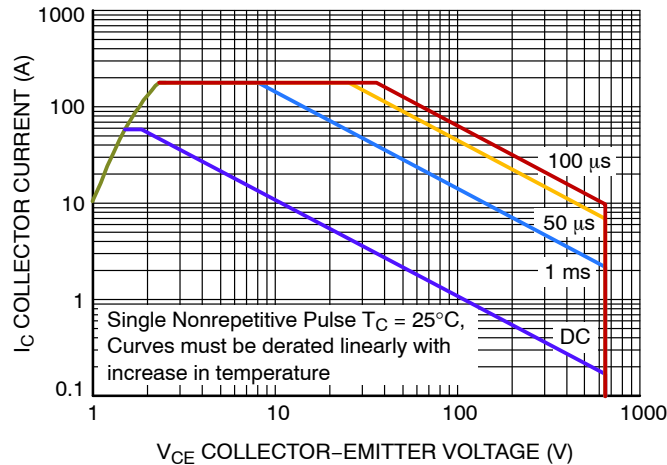


Figure 31. IGBT Safe Operating Area



# NXH75M65L4Q1SG, NXH75M65L4Q1PTG

## TYPICAL THERMAL CHARACTERISTICS

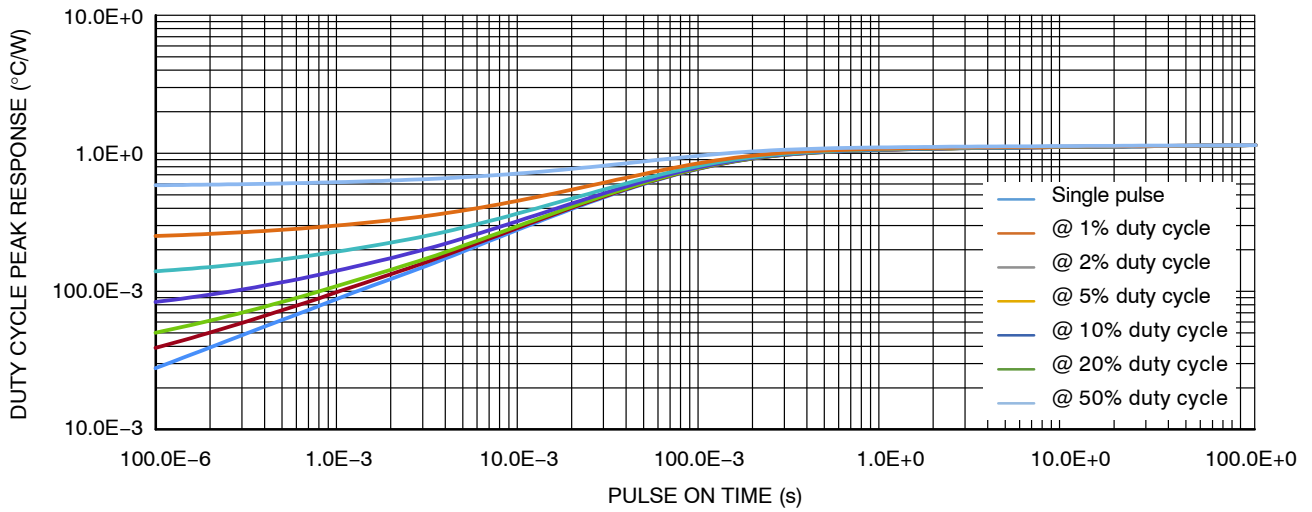


Figure 32. Transient Thermal Impedance – IGBT

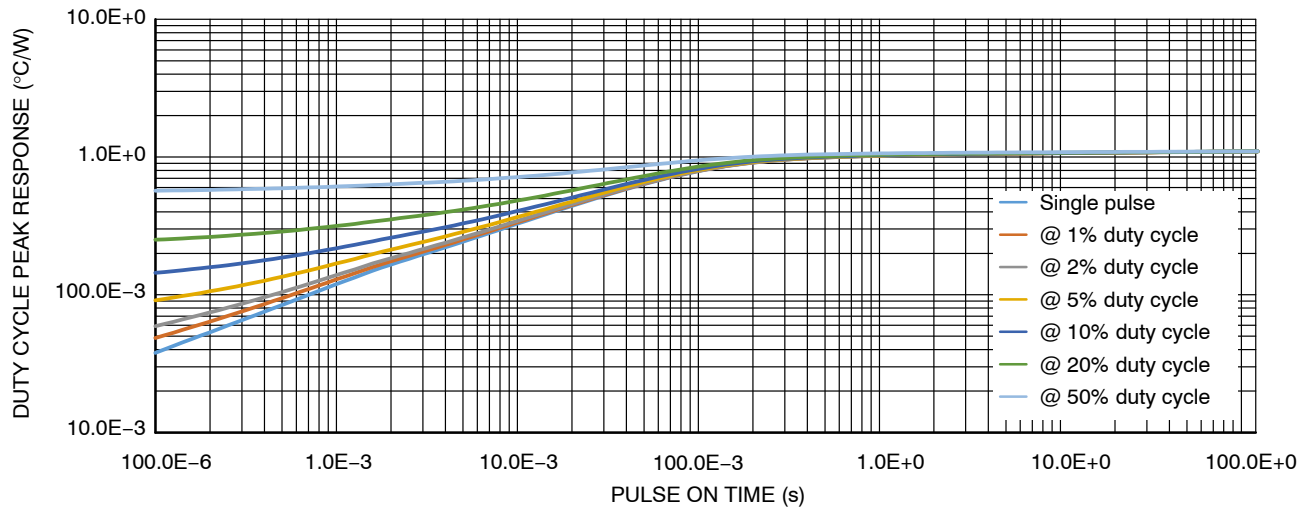


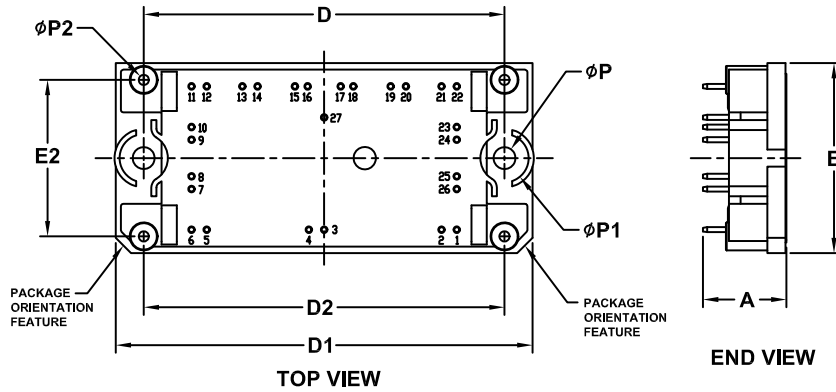
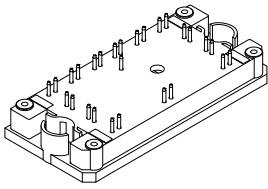
Figure 33. Transient Thermal Impedance – Diode

### ORDERING INFORMATION

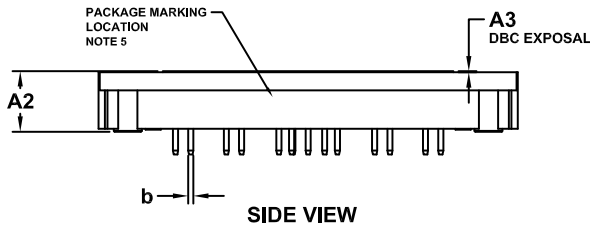
Device	Package Type	Shipping
NXH75M65L4Q1SG (Solder Pin)	PIM27, 71x37.4 Q1PACK	21 Units / BTRAY
NXH75M65L4Q1PTG (Pressfit Pin)	PIM27, 71x37.4 Q1PACK	21 Units / BTRAY

**PIM27, 71x37.4 (SOLDER PIN)**  
**CASE 180CA**  
**ISSUE B**

DATE 14 DEC 2022



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	15.90	16.40	16.90
A2	11.70	11.90	12.10
A3	0.00	0.20	0.60
b	0.95	1.00	1.05
b1	0.75	0.80	0.85
D	70.80	71.00	71.20
D1	81.70	82.00	82.30
D2	70.80	71.00	71.20
E	37.10	37.40	37.70
E2	30.60	30.80	31.00
P	4.10	4.30	4.50
P1	9.30	9.50	9.70
P2	1.80	2.00	2.20



NOTE 4

PIN	PIN POSITION		PIN	PIN POSITION	
	X	Y		X	Y
1	52.20	0.00	15	20.35	28.20
2	49.20	0.00	16	22.85	28.20
3	26.10	0.00	17	29.35	28.20
4	23.10	0.00	18	31.85	28.20
5	3.00	0.00	19	39.20	28.20
6	0.00	0.00	20	42.20	28.20
7	0.00	8.00	21	49.20	28.20
8	0.00	10.50	22	52.20	28.20
9	0.00	17.70	23	52.20	20.20
10	0.00	20.20	24	52.20	17.70
11	0.00	28.20	25	52.20	10.50
12	3.00	28.20	26	52.20	8.00
13	10.00	28.20	27	26.10	22.10
14	13.00	28.20			

NOTES:

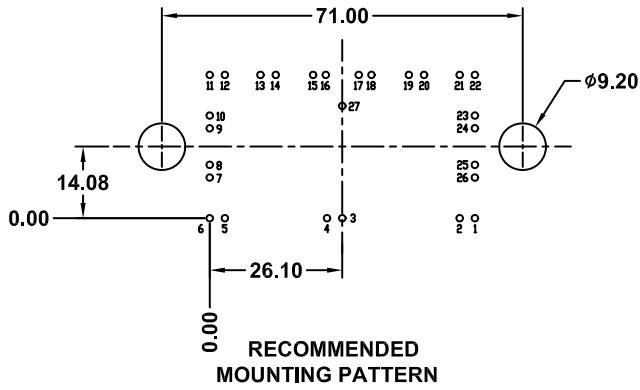
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009
2. CONTROLLING DIMENSION : MILLIMETERS
3. DIMENSIONS b AND b1 APPLY TO THE PLATED TERMINALS AND ARE MEASURED AT DIMENSION A1
4. PIN POSITION TOLERANCE IS ± 0.4mm
5. PACKAGE MARKING IS LOCATED AS SHOWN ON THE SIDE OPPOSITE THE PACKAGE ORIENTATION FEATURES

<b>DOCUMENT NUMBER:</b>	<b>98AON20006H</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>PIM27, 71x37.4 (SOLDER PIN)</b>	<b>PAGE 1 OF 2</b>

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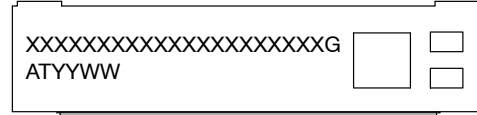
**PIM27, 71x37.4 (SOLDER PIN)**  
**CASE 180CA**  
**ISSUE B**

DATE 14 DEC 2022

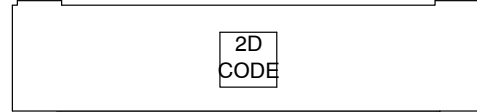


\* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**GENERIC MARKING DIAGRAM\***



FRONTSIDE MARKING



BACKSIDE MARKING

XXXXX = Specific Device Code  
 G = Pb-Free Device  
 AT = Assembly & Test Site Code  
 YYWW = Year and Work Week Code

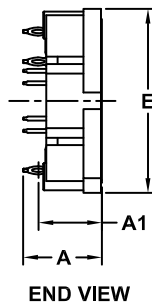
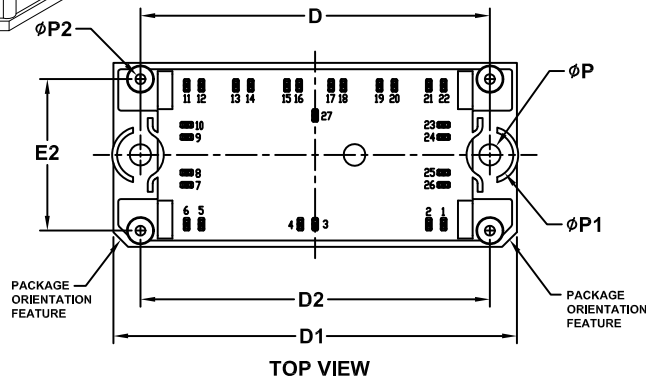
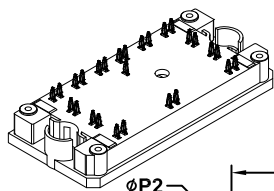
\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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<b>DESCRIPTION:</b>	<b>PIM27, 71x37.4 (SOLDER PIN)</b>	<b>PAGE 2 OF 2</b>

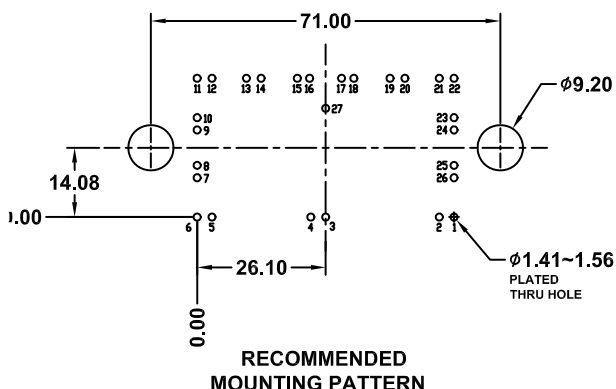
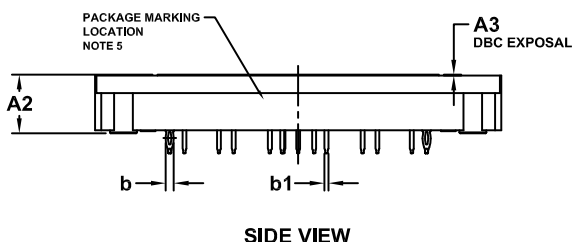
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PIM27, 71x37.4 (PRESSFIT PIN)  
CASE 180CP  
ISSUE A

DATE 20 DEC 2022



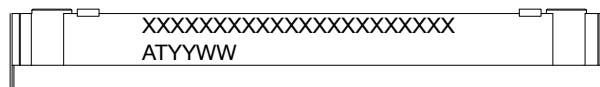
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	15.50	16.00	16.50
A1	12.38	12.88	13.38
A2	11.70	11.90	12.10
A3	0.00	0.20	0.60
b	1.61	1.66	1.71
b1	0.75	0.80	0.85
D	70.80	71.00	71.20
D1	81.70	82.00	82.30
D2	70.80	71.00	71.20
E	37.10	37.40	37.70
E2	30.60	30.80	31.00
P	4.10	4.30	4.50
P1	9.30	9.50	9.70
P2	1.80	2.00	2.20



NOTE 4

PIN	PIN POSITION		PIN	PIN POSITION	
	X	Y		X	Y
1	52.20	0.00	15	20.35	28.20
2	49.20	0.00	16	22.85	28.20
3	26.10	0.00	17	29.35	28.20
4	23.10	0.00	18	31.85	28.20
5	3.00	0.00	19	39.20	28.20
6	0.00	0.00	20	42.20	28.20
7	0.00	8.00	21	49.20	28.20
8	0.00	10.50	22	52.20	28.20
9	0.00	17.70	23	52.20	20.20
10	0.00	20.20	24	52.20	17.70
11	0.00	28.20	25	52.20	10.50
12	3.00	28.20	26	52.20	8.00
13	10.00	28.20	27	26.10	22.10
14	13.00	28.20			

GENERIC  
MARKING DIAGRAM\*



XXXXX = Specific Device Code  
AT = Assembly & Test Site Code  
YYWW = Year and Work Week Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009
2. CONTROLLING DIMENSION : MILLIMETERS
3. DIMENSIONS b AND b1 APPLY TO THE PLATED TERMINALS AND ARE MEASURED AT DIMENSION A1
4. PIN POSITION TOLERANCE IS  $\pm 0.4\text{mm}$
5. PACKAGE MARKING IS LOCATED AS SHOWN ON THE SIDE OPPOSITE THE PACKAGE ORIENTATION FEATURES

\* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	PIM27, 71X37.4 (PRESSFIT PIN)	PAGE 1 OF 1

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